Open Quantum Systems Answers to Exercise Set 1 - JPBK

Jake Muff jake.muff@helsinki.fi Student number: 015361763 25/09/2020

1. Problem 1.1

(a) Obtain

$$I = \frac{1}{eR_T} \int d\epsilon \ n_L(\epsilon) n_R(\epsilon + eV) [f_l(\epsilon) - f_R(\epsilon + eV)]$$

To do this we substitute in the forward and backward tunneling rates into

$$I = e(\Gamma_f - \Gamma_b) \tag{1}$$

Noticing that the "transparancy" value is equal[1] to

$$|\tau|^2 = \frac{1}{e^2 R_T}$$

$$I = e(|\tau|^2 \int d\epsilon \ n_L(\epsilon) f_L(\epsilon) n_R(\epsilon + eV) [1 - f_R(\epsilon + eV)]$$

$$-|\tau|^2 \int d\epsilon \ n_R(\epsilon + eV) f_R(\epsilon + eV) n_L(\epsilon) [1 - f_L(\epsilon)])$$

$$I = e|\tau|^2 \int n_L(\epsilon) f_L(\epsilon) n_R(\epsilon + eV) - n_L(\epsilon) n_R(\epsilon + eV) f_R(\epsilon + eV) d\epsilon$$

$$= e|\tau|^2 \int d\epsilon \ n_L(\epsilon) n_R(\epsilon + eV) [f_L(\epsilon) - f_R(\epsilon + eV)]$$

$$= \frac{1}{eR_T} \int d\epsilon \ n_L(\epsilon) n_R(\epsilon + eV) [f_L(\epsilon) - f_R(\epsilon + eV)]$$

2. Problem 1.2

The left and right electrode temperatures have occuptation of energy levels as describes by the fermi distribution

$$f_{L,R}(\epsilon) = \frac{1}{1 + \exp((\epsilon - \epsilon_{f,L(R)})/k_B T_{L,R})}$$
(2)

So that we define

$$\epsilon_{F,L(R)} = 0$$
 and $\epsilon_{f,R} = \epsilon - eV$

Applying electron hole symmetry we get equation 18 in the lecture notes. The density of states is approximately constant close to the fermi energy so we have

$$n_{L,R}(\epsilon) = 1.$$

Using the fermi distribution above and equations 18 from the lecture notes for the forward and backward tunneling rates we get

$$\Gamma_{f,b}(V) = \frac{1}{e^2 R_T} \frac{\pm eV}{1 - \exp(\mp eV/k_B T)}$$

Which is the same as

$$\Gamma = \frac{1}{e^2 R_T} \frac{eV}{1 - \exp(-eV\beta)}$$

Assuming of course that $T_L = T_R = T = \frac{1}{k_B \beta}$

Substituting the above equation with these assumptions into (1) gives a linear relationship such that $I(V) = \frac{V}{R_T}$ showing that the junction is ohmic.

3. Problem 1.3 For problem 1.3 we are looking at a NIS junction at low temperatures where $eV, k_BT \ll \Delta$. For this we can use the Bardeen-Cooper-Schrieffer theory of superconductors where electrons form a condensate of cooper pairs that occupy the ground state below the critical temperature. Single electron excitations in the superconductor are separated from the ground state by a gap labelled Δ such that

$$n_s(\epsilon) = n_s(0) \begin{cases} \frac{|\epsilon|}{\sqrt{\epsilon^2 - \Delta^2}} & \text{for } |\epsilon| > \Delta \\ 0 & |\epsilon| < \Delta \end{cases}$$

Where $n_s(0)$ is constant and equivalent to $n_R(\epsilon)$ in the notes.

To answer this lets change some notation and introduce [2] a new factor G_{NIN} to represent the conductance for the NIN junction that is independent of V.

$$I_{NIN} = \frac{1}{eR_T} \int d\epsilon \ n_L(\epsilon) n_R(\epsilon + eV) [f_L(\epsilon) - f_R(\epsilon + eV)]$$
$$I_{NIN} = G_{NIN} V$$

We can make this relation as it is ohmic. Such that we can now write the tunnelign current for NIS as

$$I_{NIS} = \frac{G_{NIN}}{e} \int d\epsilon \ n_s(\epsilon) [f_s(\epsilon) - f_N(\epsilon + eV)]$$

And our conductance G_{NIS} for the NIS junction is

$$G_{NIS} = \frac{dI_{NIS}}{dV} = G_{NIN} \int n_s(\epsilon) \left[-\frac{\partial f_N(\epsilon + eV)}{\partial (eV)} \right] d\epsilon$$

The conductance at V=0 is related to the width of the gap Δ through evaluating the derivatives over each other. We can now introduce our low temperature conditions.

For $k_BT \ll \Delta$

$$\left. \frac{G_{NIS}}{G_{NIN}} \right|_{V=0} = \sqrt{\frac{2\pi\Delta}{k_B T}} e^{-\Delta/k_b T}$$

For voltages $eV \ll \Delta$ this changes to

$$\sqrt{2\pi\Delta k_B T}e^{-(\Delta-eV)/k_B T}$$

Where $I_0 = \sqrt{2\pi\Delta k_B T}$

We could take this further if we introduced the Dynes density of states, however I have kept to using the BCS DoS

References

- [1] Anna Feshchenko *Electron Themometry, refrigeration and heat transport in nanos-tructures at sub-kelvin temperatures* Doctoral Thesis, Department of Applied Physics, Low Temperature Laboratory, Aalto University
- [2] M. Tinkham Introduction to Superconductivity Dover Publications, 2004